

In the claims:

Please amend claim 1, cancel claim 5, and add new claim 10, as presented.

What is claimed is:

1. (Currently Amended) A semiconductor laser device comprising a semiconductor laser element or a plurality of individual lasers mounted in parallel with a plurality of exit surfaces from which laser light can emerge which in a first direction (Y) has greater divergence than in the second direction which is perpendicular to it; and at least one reflection means which is located spaced apart from the exit surfaces outside of the semiconductor laser element or of the plurality of individual lasers, with at least one reflecting surface of concave curvature which can reflect back at least parts of the laser light which has emerged from the semiconductor laser element or the plurality of individual lasers through the exit surfaces into the semiconductor laser element or the plurality of individual lasers such that the mode spectrum of the semiconductor laser element or of the individual lasers is influenced thereby; wherein ~~at least one reflecting surface of the reflection means is concavely curved~~ the at least one reflecting means comprises a plurality of individual reflecting surfaces, each individual reflecting surface reflects one sub-beam being emitted from one individual exit surface.

2. (Previously Presented) The semiconductor laser device as claimed in claim 1, wherein at least one reflecting surface can reflect back component beams of laser light onto the exit surfaces such that they are used as an aperture.

3. (Previously Presented) The semiconductor laser device as claimed in claim 1, wherein the semiconductor laser device comprises a lens means which is located between the reflection means and the semiconductor laser element or the plurality of individual

lasers and which can at least partially reduce the divergence of the laser light at least in the first direction (Y).

4. (Previously Presented) The semiconductor laser device as claimed in claim 1, wherein the at least one reflection means has a reflecting surface on which component beams emerging from different exit surfaces can be reflected.

5. (Cancelled)

6. (Previously Presented) The semiconductor laser device as claimed in claim 1, wherein the semiconductor laser device comprises a beam transformation unit which is beam rotation unit and can rotate individual ones of the component beams at one time, by roughly 90°.

7. (Previously Presented) The semiconductor laser device as claimed in claim 6, wherein the beam transformation unit is located between the at least one reflection means and the semiconductor laser element or the plurality of individual lasers, between the at least one reflection means and the lens means.

8. (Previously Presented) The semiconductor laser device as claimed in claim 1, wherein the semiconductor laser device further comprises a frequency-doubling element which is located between the at least one reflection means and the semiconductor laser element or the plurality of individual lasers, between the at least one reflection means and the lens means.

9. (Previously Presented) The semiconductor laser device as claimed in claim 1, wherein the semiconductor laser element is exposed to a voltage and is supplied with current for producing

electron-hole pairs only in partial areas which correspond to the three-dimensional extension of the desired mode of the laser light.

10. (New) The semiconductor laser device as claimed in claim 1, wherein the plurality of individual reflecting surfaces reflects all of the laser light impinging on the plurality of individual reflecting surfaces.